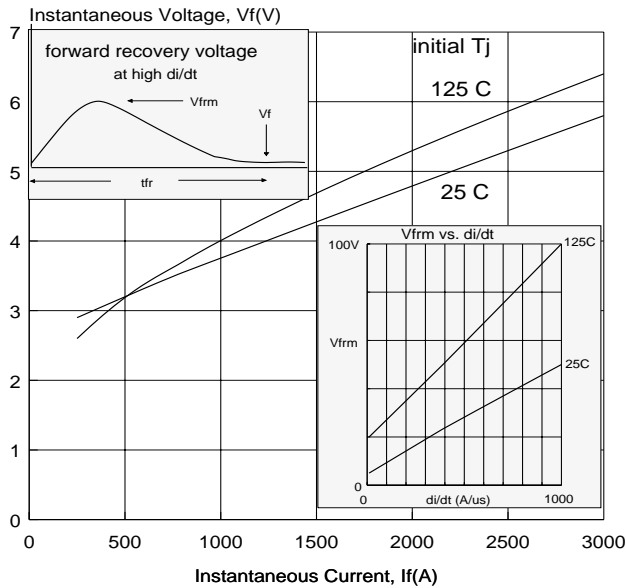


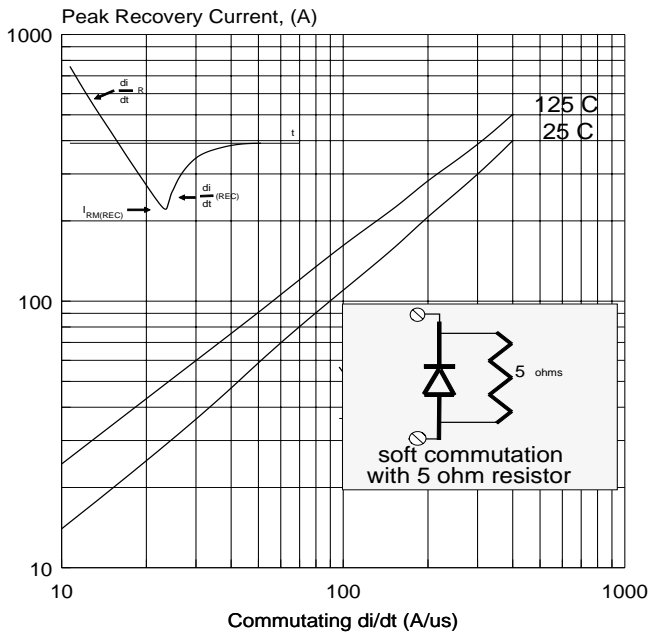
The SDD63HK fast recovery diode is designed for use in complex snubber circuits commonly used for gate turn-off thyristors, GTO's, for which the low forward recovery voltage developed by the diode at extremely high di/dt is important in order to achieve full turn-off capability. It is manufactured by the proven multi-diffusion process and is supplied in a disc-type package, ready to mount using commercially available heat dissipators and clamping hardware.

Forward EI Characteristic - typical  
8 ms pulse



T63 5/11/90

Peak Recovery Current  
typical diode



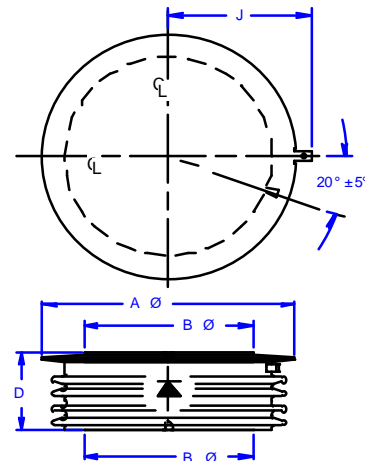
T63 5/10/90

**Principal Ratings and Characteristics**

Repetitive peak reverse voltage	$V_{RRM}$	$T_j = -40$ to 125°C	up to 4500	V
Peak forward recovery voltage	$V_{FRM}$	@1000A/us	50	V
Forward recovery time	$t_{fr}$	@1000A/us	2	us
Forward turn-on time	$t_{on}$	$I_F = 1000A$	4	us
Peak forward drop	$V_f$	@ $I_F = 1000A$	5	V

Note: All values are maximum at 25°C unless noted.

**MECHANICAL OUTLINE**



$AF = 2.30$  in (58.0 mm)  
 $BF = 1.35$  in (34.3 mm)  
 $D = 1.04$  in (26.4 mm)

ALLOWABLE RANGE CLAMPING FORCE  
450 - 3500 lb / 2 - 16 kN